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APPLICANT
Makoto KITABATAKE, et al.

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EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		LUTZ et al., Technische Universität Chemnitz, "Stand und Entwicklungstendenzen bei schnellen Dioden," 20020301, 1 March 2002 (2002-03-01), XP002491991; and partial English translation thereof
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EXAMINER /Abul Kalam/		DATE CONSIDERED 10/21/2009

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.K./